

BB301M

Build in Biasing Circuit MOS FET IC
VHF RF Amplifier

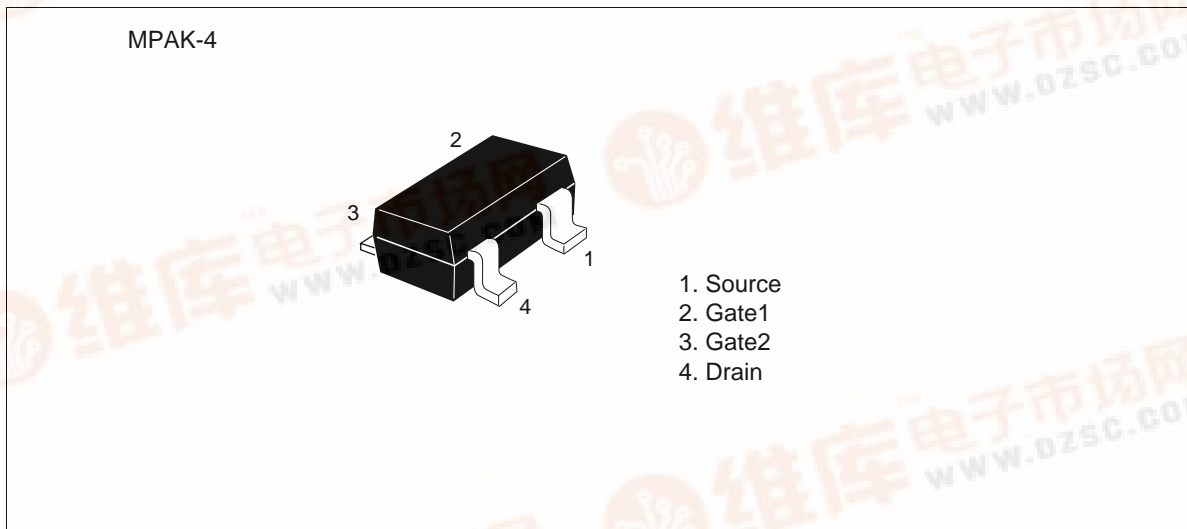
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ADE-208-506
1st. Edition

Features

- Build in Biasing Circuit; To reduce using parts cost & PC board space.
- Low noise characteristics; (NF = 1.3 dB typ. at f = 200 MHz)
- Withstanding to ESD; Build in ESD absorbing diode. Withstand up to 200 V at C = 200 pF, Rs = 0 conditions.

Outline



BB301M

Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Ratings	Unit
Drain to source voltage	V_{DS}	6	V
Gate 1 to source voltage	V_{G1S}	+6 -0	V
Gate 2 to source voltage	V_{G2S}	±6	V
Drain current	I_D	25	mA
Channel power dissipation	Pch	150	mW
Channel temperature	Tch	150	°C
Storage temperature	Tstg	-55 to +150	°C

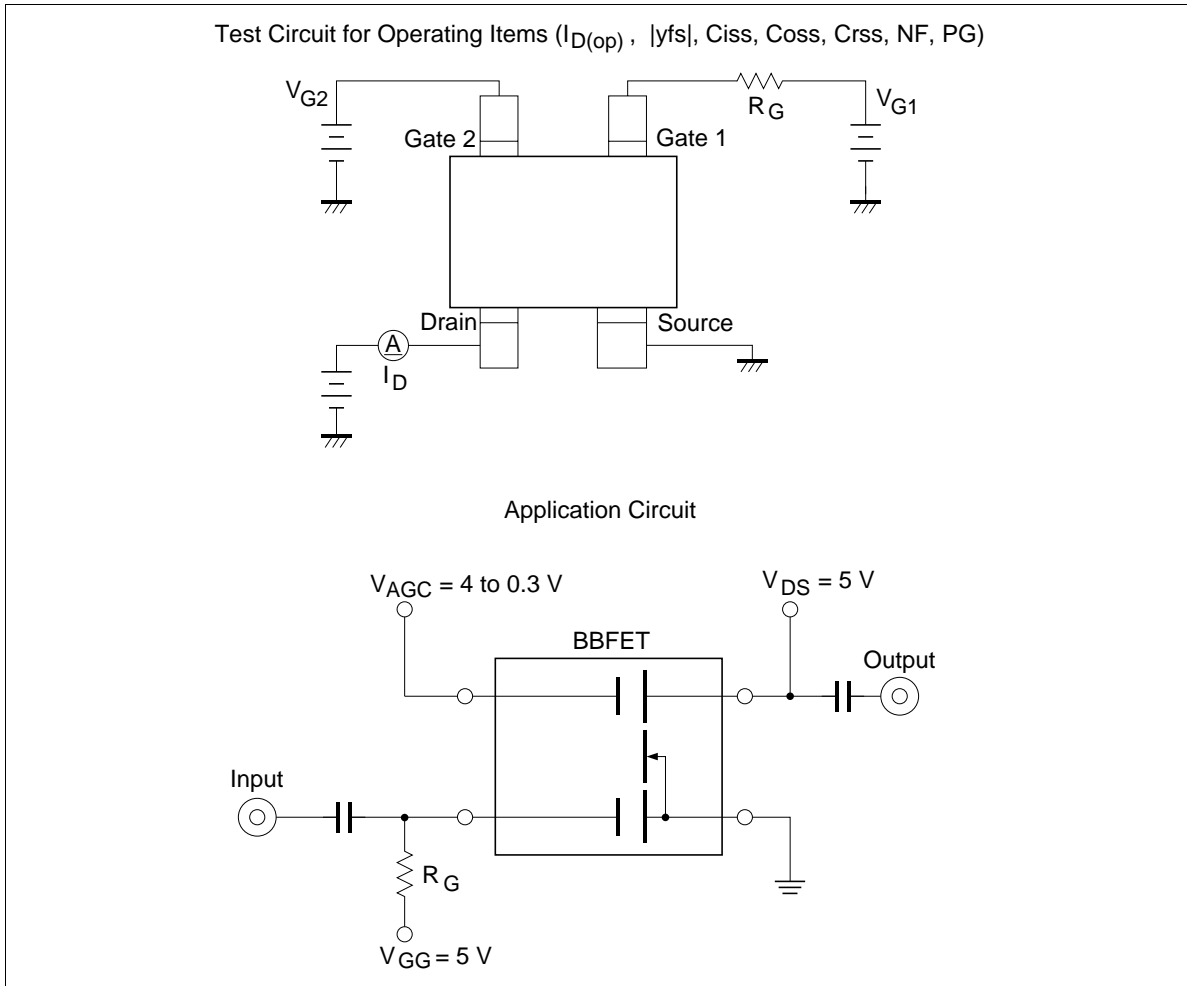
Electrical Characteristics (Ta = 25°C)

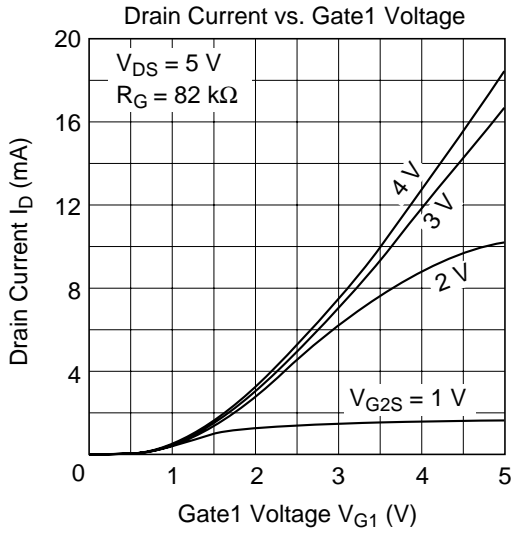
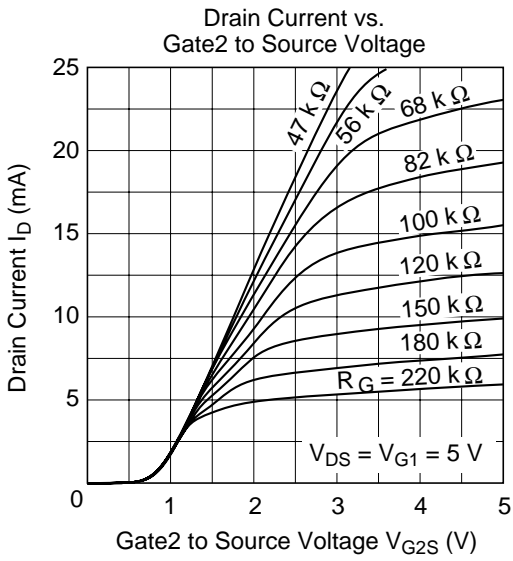
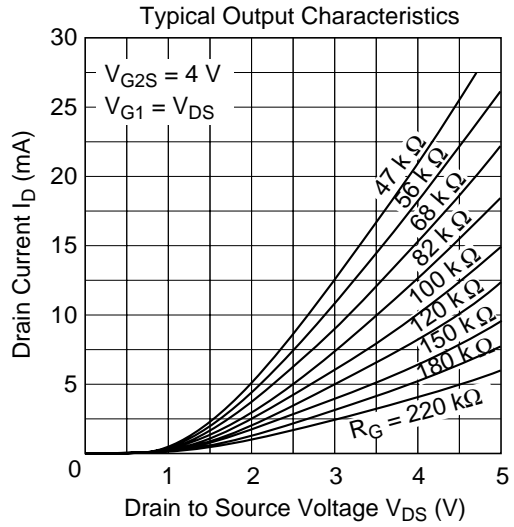
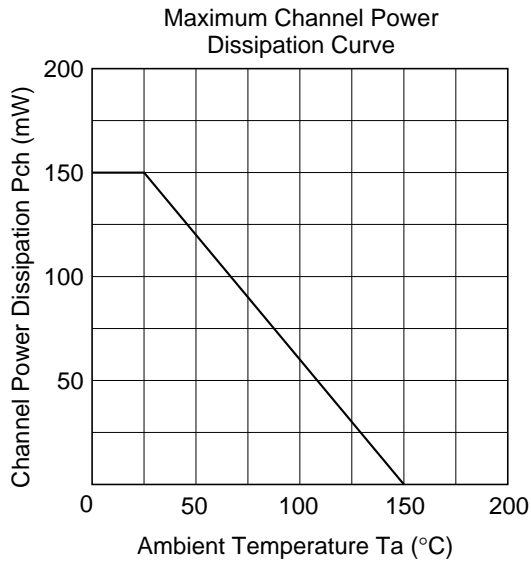
Item	Symbol	Min	Typ	Max	Unit	Test conditions
Drain to source breakdown voltage	$V_{(BR)DSS}$	6	—	—	V	$I_D = 200 \mu A$ $V_{G1S} = V_{G2S} = 0$
Gate 1 to source breakdown voltage	$V_{(BR)G1SS}$	+6	—	—	V	$I_{G1} = +10 \mu A$ $V_{G2S} = V_{DS} = 0$
Gate 2 to source breakdown voltage	$V_{(BR)G2SS}$	± 6	—	—	V	$I_{G2} = \pm 10 \mu A$ $V_{G1S} = V_{DS} = 0$
Gate 1 to source cutoff current	I_{G1SS}	—	—	+100	nA	$V_{G1S} = +5 V$ $V_{G2S} = V_{DS} = 0$
Gate 2 to source cutoff current	I_{G2SS}	—	—	± 100	nA	$V_{G2S} = \pm 5 V$ $V_{G1S} = V_{DS} = 0$
Gate 1 to source cutoff voltage	$V_{G1S(off)}$	0.4	—	1.0	V	$V_{DS} = 5 V, V_{G2S} = 4 V$ $I_D = 100 \mu A$
Gate 2 to source cutoff voltage	$V_{G2S(off)}$	0.4	—	1.0	V	$V_{DS} = 5 V, V_{G1S} = 5 V$ $I_D = 100 \mu A$
Drain current	$I_{D(op)}$	10	15	20	mA	$V_{DS} = 5 V, V_{G1} = 5 V$ $V_{G2S} = 4 V, R_G = 100 k\Omega$
Forward transfer admittance	$ y_{fs} $	15	20	—	mS	$V_{DS} = 5 V, V_{G1} = 5 V$ $V_{G2S} = 4 V$ $R_G = 100 k\Omega, f = 1 kHz$
Input capacitance	Ciss	2.2	3.0	4.0	pF	$V_{DS} = 5 V, V_{G1} = 5 V$
Output capacitance	Coss	0.9	1.2	1.6	pF	$V_{G2S} = 4 V, R_G = 100 k\Omega$
Reverse transfer capacitance	Crss	—	0.018	0.04	pF	$f = 1 MHz$
Power gain	PG	22	26	—	dB	$V_{DS} = 5 V, V_{G1} = 5 V$ $V_{G2S} = 4 V$
Noise figure	NF	—	1.3	1.9	dB	$R_G = 100 k\Omega, f = 200 MHz$

Note: Marking is "AW-".

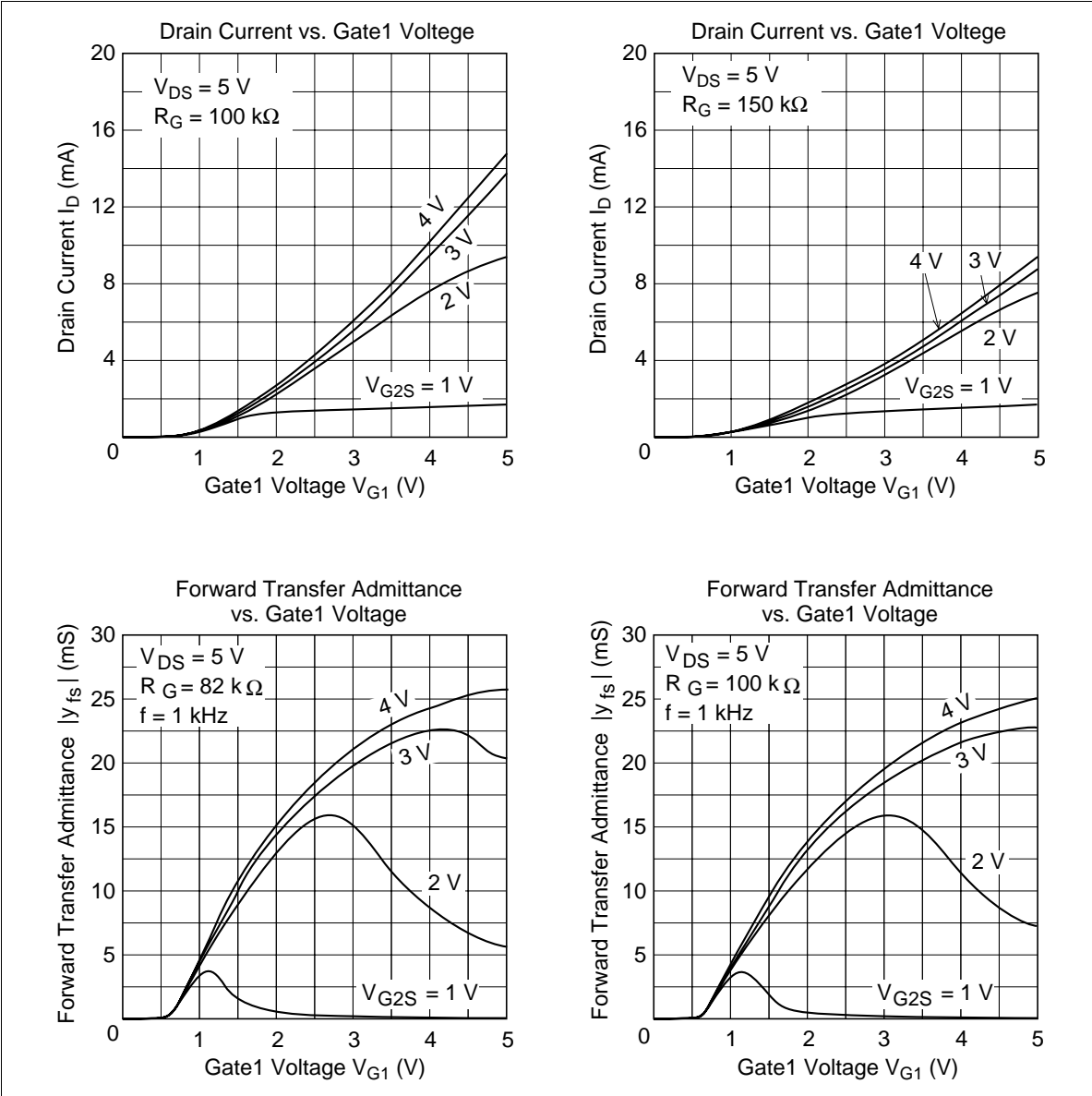
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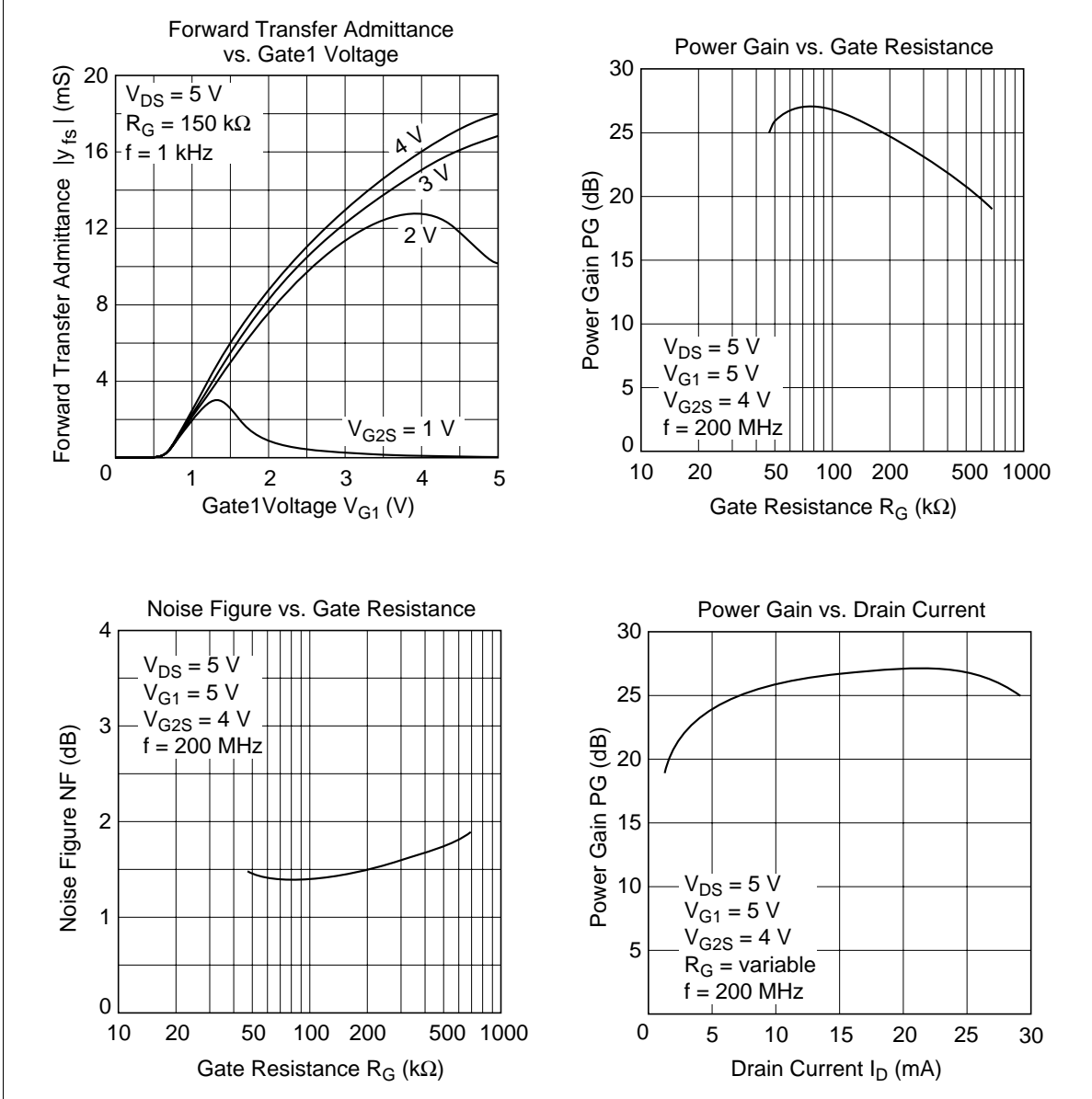
Main Characteristics



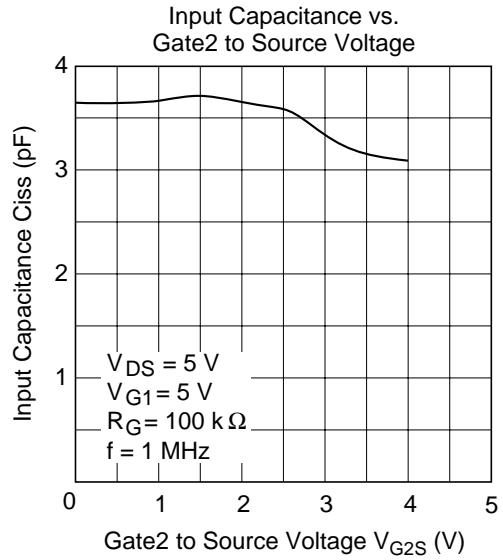
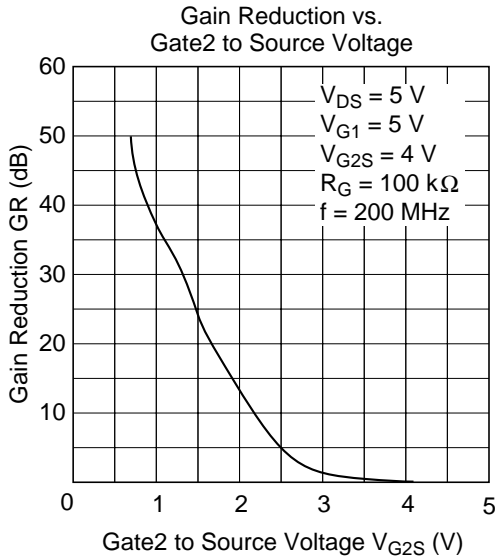
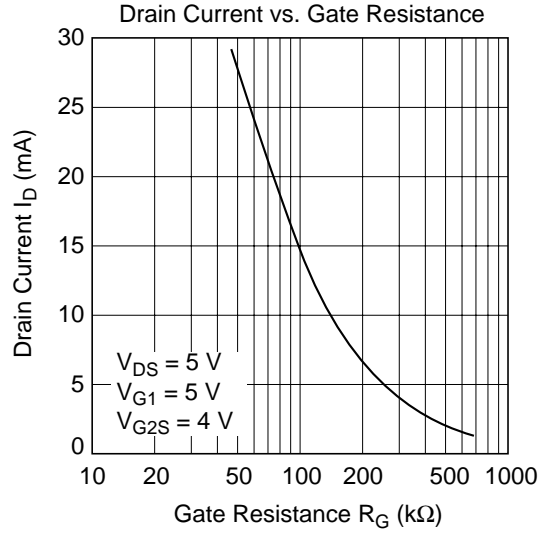
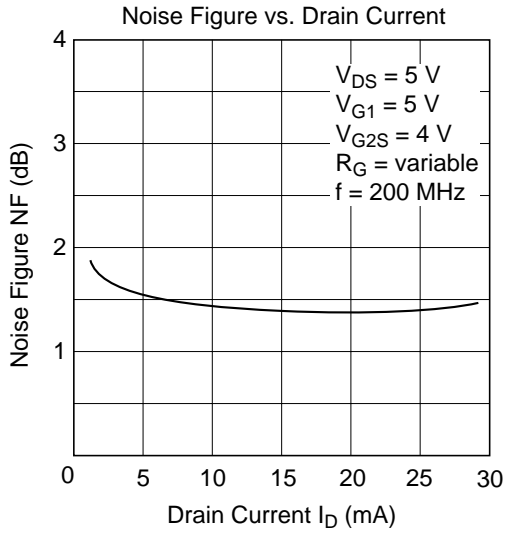


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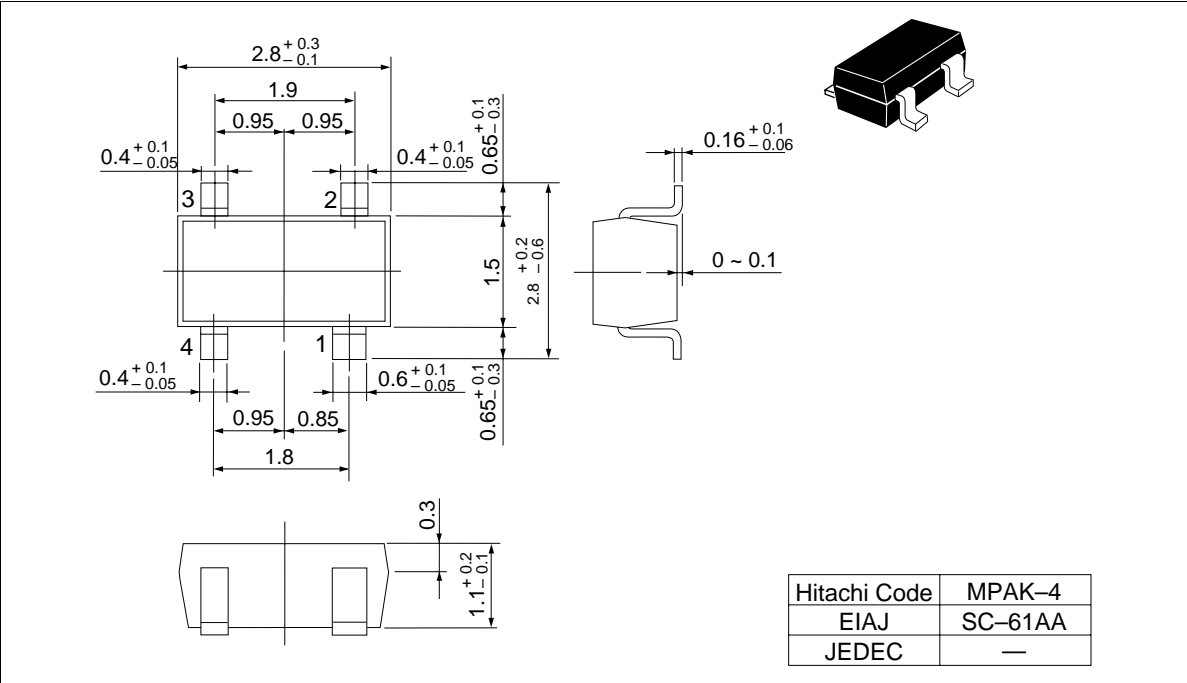


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Package Dimentions

Unit: mm



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